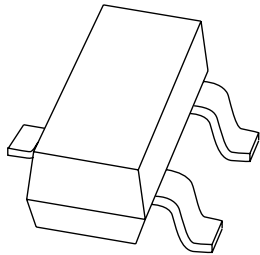


DATA SHEET



BCW29; BCW30 PNP general purpose transistors

Product data sheet
Supersedes data of 1999 Apr 13

2004 Jan 13



PNP general purpose transistors

BCW29; BCW30

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 32 V).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

PNP transistor in a SOT23 plastic package.
NPN complements: BCW31 and BCW32.

MARKING

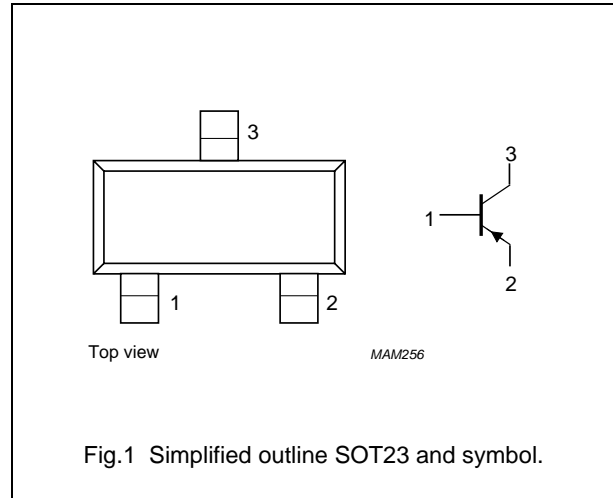
TYPE NUMBER	MARKING CODE ⁽¹⁾
BCW29	C1*
BCW30	C2*

Note

- * = p : Made in Hong Kong.
* = t : Made in Malaysia.
* = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BCW29	-	plastic surface mounted package; 3 leads	SOT23
BCW30			

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	-	-32	V
V _{CEO}	collector-emitter voltage	open base; I _C = -2 mA	-	-32	V
V _{EBO}	emitter-base voltage	open collector	-	-5	V
I _C	collector current (DC)		-	-100	mA
I _{CM}	peak collector current		-	-200	mA
I _{BM}	peak base current		-	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	-	250	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

PNP general purpose transistors

BCW29; BCW30

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -32\text{ V}$	–	–	–100	nA
		$I_E = 0; V_{CB} = -32\text{ V}; T_j = 100\text{ }^\circ\text{C}$	–	–	–10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	–	–	–100	nA
h_{FE}	DC current gain	$I_C = -10\text{ }\mu\text{A}; V_{CE} = -5\text{ V}$	–	90	–	
			–	150	–	
	DC current gain	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V}$	120	–	260	
			215	–	500	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	–	–80	–300	mV
		$I_C = -50\text{ mA}; I_B = -2.5\text{ mA}$	–	–150	–	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	–	–720	–	mV
		$I_C = -50\text{ mA}; I_B = -2.5\text{ mA}$	–	–810	–	mV
V_{BE}	base-emitter voltage	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V}$	–600	–	–750	mV
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	4.5	–	pF
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure	$I_C = -200\text{ }\mu\text{A}; V_{CE} = -5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	–	–	10	dB

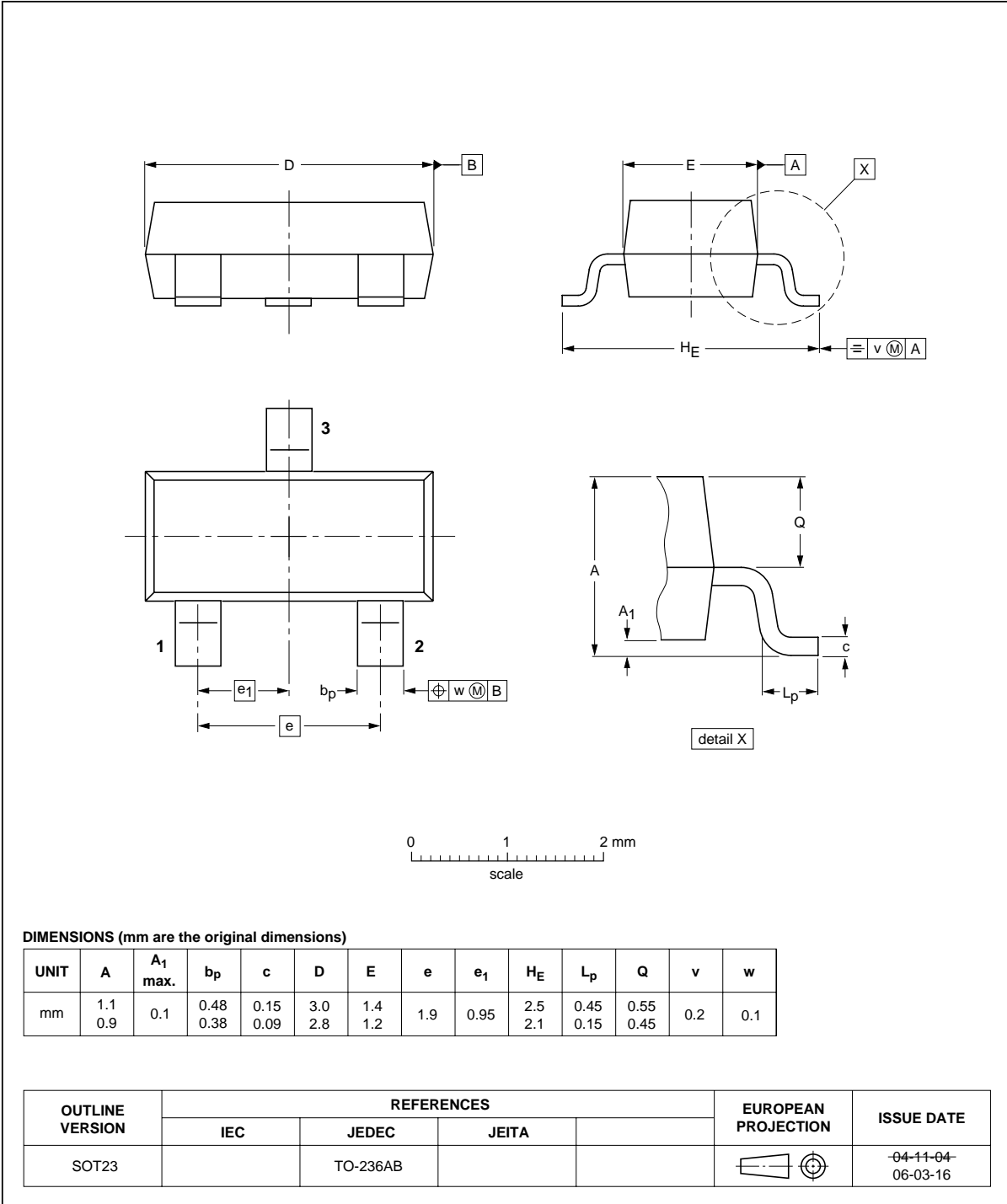
PNP general purpose transistors

BCW29; BCW30

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



PNP general purpose transistors

BCW29; BCW30

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

1. Please consult the most recently issued document before initiating or completing a design.
2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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